

JUNCTION FIELD EFFECT TRANSISTOR 2SK1109

N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR FOR IMPEDANCE CONVERTER OF ECM

DESCRIPTION

The 2SK1109 is suitable for converter of ECM.

FEATURES

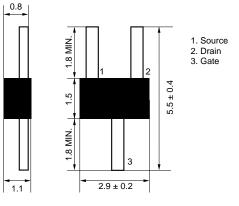
- Compact package
- High forward transfer admittance 1000 μS TYP. (Ibss = 100 μA) 1600 μS TYP. (Ibss = 200 μA)
- Includes diode and high resistance at G S

ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK1109	SC-59 (MM)		

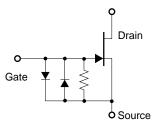
ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage Note	Vdsx	20	V
Gate to Drain Voltage	Vgdo	-20	V
Drain Current	lо	10	mA
Gate Current	lg	10	mA
Total Power Dissipation	P⊤	80	mW
Junction Temperature	Tj	125	°C
Storage Temperature	Tstg	-55 to +125	°C



PACKAGE DRAWING (Unit: mm)

EQUIVALENT CIRCUIT



Note Vgs = -1.0 V

Remark Please take care of ESD (Electro Static Discharge) when you handle the device in this document.

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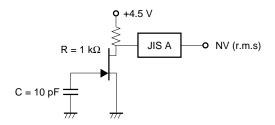
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNIT
Zero Gate Voltage Drain Cut-off Current	IDSS	$V_{DS} = 5.0 V, V_{GS} = 0 V$	40		600	μA
Gate Cut-off Voltage	VGS(off)	$V_{DS} = 5.0 \text{ V}, \text{ ID} = 1.0 \ \mu\text{A}$	-0.1		-1.0	V
Forward Transfer Admittance	y _{fs1}	$V_{DS} = 5.0 \text{ V}, \text{ ID} = 30 \ \mu\text{A}, \text{ f} = 1.0 \text{ kHz}$	350			μS
Forward Transfer Admittance	yfs2	$V_{DS} = 5.0 V$, $V_{GS} = 0 V$, $f = 1.0 \text{ kHz}$	350			μS
Input Capacitance	Ciss	$V_{DS} = 5.0 V, V_{GS} = 0 V, f = 1.0 MHz$		7.0	8.0	pF
Noise Voltage	NV	See Test Circuit		1.8	3.0	μV

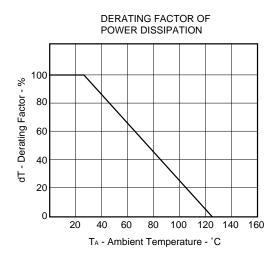
IDSS RANK

MARKING	J32	J33	J34	J35	J36	J37
lɒss (μΑ)	40 to 70	60 to 110	90 to 180	150 to 300	200 to 450	300 to 600

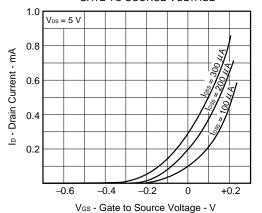
NOISE VOLTAGE TEST CIRCUIT



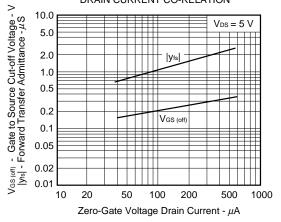
TYPICAL CHARACTERISTICS (TA = 25°C)

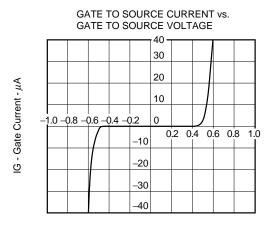






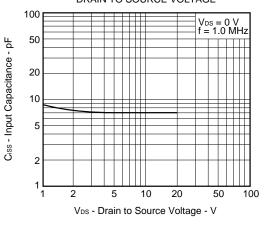
GATE TO SOURCE CUT-OFF VOLTAGE AND FORWARD TRANSFER ADMITTANCE vs. ZERO-GATE VOLTAGE DRAIN CURRENT CO-RELATION

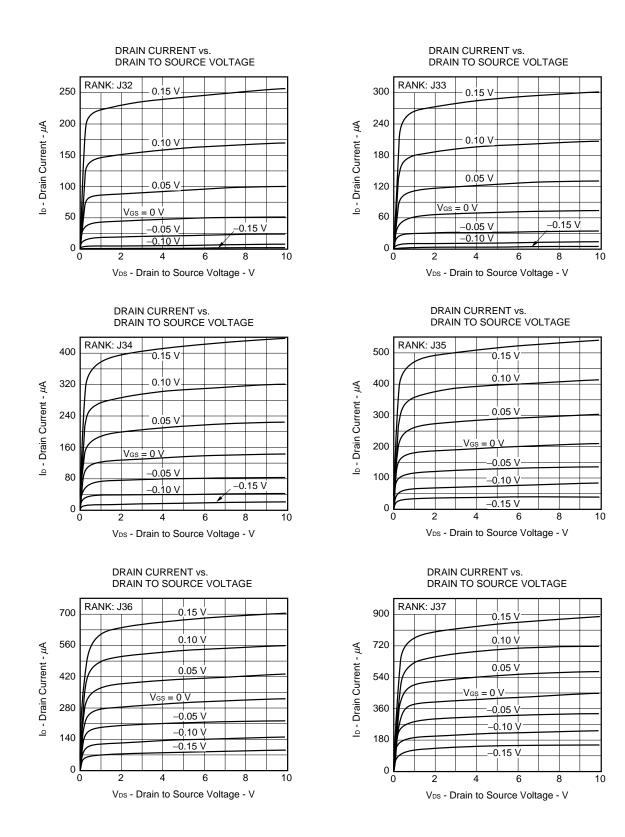




VGS - Gate to Source Voltage - V

INPUT CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE





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